Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A method for forming a junction in a semiconductor device, comprising the steps of:

forming a photoresist film pattern on a semiconductor substrate excluding a first region;

performing a first halo implant process twice on the first region of the semiconductor substrate by using a tilt angle of about 45° and twist angles of 0° and 180°; and

performing a second halo implant process on the first region of the semiconductor substrate by using a tilt angle of about 0°, said first and second halo implant processes being performed at substantially the same dose.

2. (Previously presented) The method according to claim 1, wherein the first halo implant process is performed with an energy of 20KeV and a dose of 4.0×10^{12} ions/cm^2.

3. (Canceled)

4. (Previously presented) The method according to claim 1, wherein the second halo implant process is performed only once at a tilt angle of about 0°.

5. (Currently Amended) The method according to claim 1, wherein the second halo implant process is performed with an energy of 16KeV and a dose of 4×10^{12} ions/cm^2.

6. (Original) The method according to claim 1, wherein the photoresist film pattern is formed on a PMOS region, and the first region is an NMOS region.

7. (Original) The method according to claim 1, wherein the photoresist film pattern is formed on an NMOS region, and the first region is a PMOS region.

8. (Currently Amended) A method for forming a junction in a semiconductor device, comprising the steps of:

providing a semiconductor substrate divided into a first conductive type MOS region and a second conductive type MOS region;

forming a photoresist film pattern on the second conductive type MOS region;

performing first and second halo implant processes on the first conductive type MOS region at about a 45° tilt angle and at twist angles of about 0° and 180°, respectively; and

performing a third halo implant process on the first conductive type MOS region, by using a tilt angle of about 0°~~, said first, second and third halo implant processes being performed at substantially the same dose~~.

9. (Previously Presented) The method according to claim 8, wherein the first halo implant process is performed with an energy of 20KeV and a dose of $4.0x10^{12}$ ions/cm^2.

10. (Previously Presented) The method according to claim 8, wherein the second halo implant process is performed with an energy of 20KeV and a dose of $4.0x10^{12}$ ions/cm^2.

11. (Previously Presented) The method according to claim 8, wherein the third halo implant process is performed with an energy of 16KeV and a dose of $4x10^{12}$ ions/cm^2.

12. (Original) The method according to claim 8, wherein the first conductive type MOS region is an NMOS region, and the second conductive type MOS region is a PMOS region.

13. (original) The method according to claim 8, wherein the first conductive type MOS region is a PMOS region, and the second conductive type MOS region is an NMOS region.

14. (Previously Presented) The method of claim 1, wherein the first and second halo implants are homogenously doped.

15. (Previously Presented) The method of claim 8, wherein the first and second halo implants are homogenously doped.